

## MICROWAVE POWER GAAS FET

# TIM5964-35SLA

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 45.5dBm at 5.9GHz to 6.4GHz

·HIGH GAIN

G1dB= 9.0dB at 5.9GHz to 6.4GHz

**LOW INTERMODULATION DISTORTION** 

IM3(MIN.)= -42dBc at Pout= 35dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



## RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 8.0A f= 5.9 to 6.4GHz  Two-Tone Test Po= 35dBm, Δf= 5MHz (Single Carrier Level)	dBm	45.0	45.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	9.0	_
Drain Current	IDS1		Α	_	8.0	9.0
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%	_	39	_
3rd Order Intermodulation Distortion	IM3		dBc	-42	-45	_
Drain Current	IDS2		Α	_	8.0	9.0
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_		100

Recommended Gate Resistance(Rg): 28 Ω

## **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.5A	S	_	6.5	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 140mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	20	_
Gate-Source Breakdown Voltage	VGSO	IGS= -420 <sub>μ</sub> A	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.0	1.3

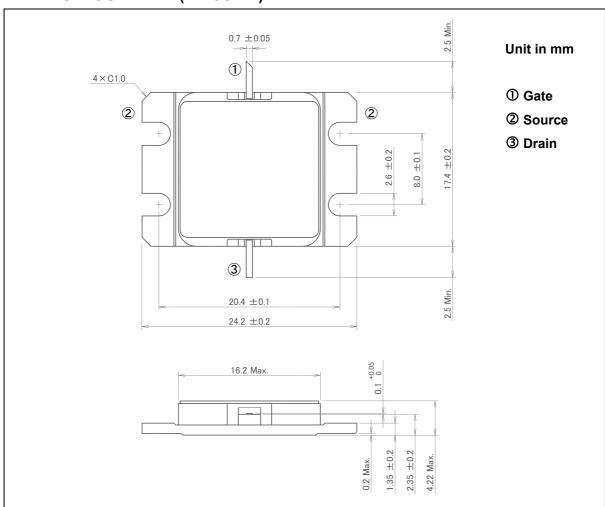
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## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20
Total Power Dissipation (Tc= 25°C)	PT	W	115.4
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

## PACKAGE OUTLINE (2-16G1B)



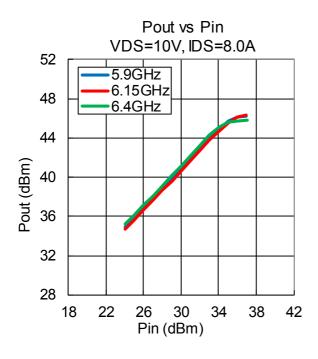
## HANDLING PRECAUTIONS FOR PACKAGE MODEL

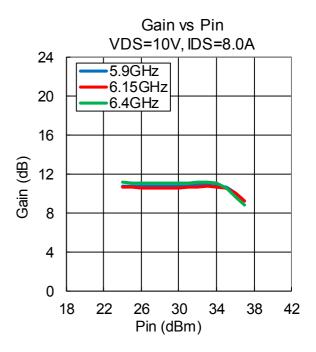
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

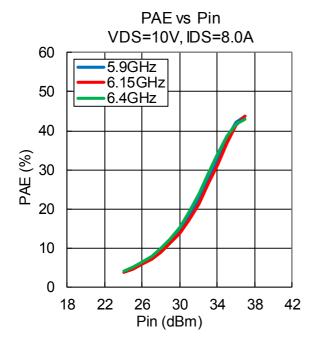
### **TYPICAL RF PERFORMANCE**

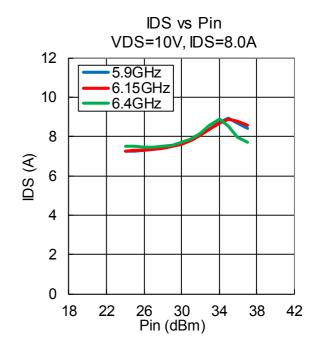
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 8.0 A, f= 5.9, 6.15, 6.4 GHz, Ta= +25 °C





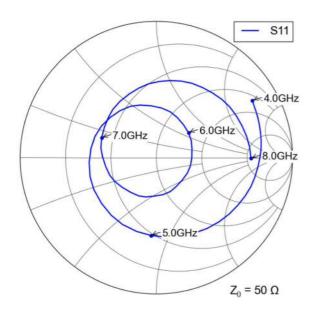


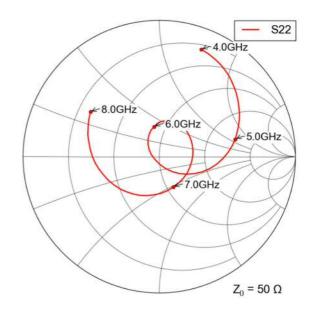


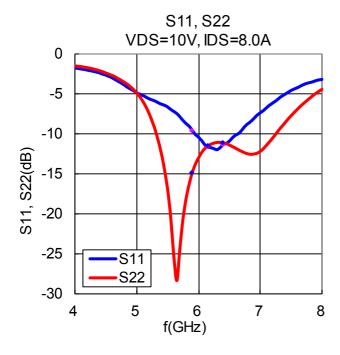


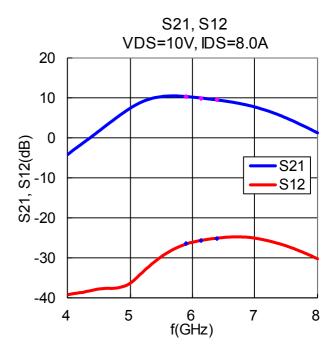
#### ·S-Parameters

VDS= 10 V, IDSset= 8.0 A, f= 4.0 to 8.0 GHz, Ta= +25  $^{\circ}$ C











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